KSW04N100

1000V N-Channel MOSFET

General Description

The KSW04N100 is the silicon N-channel Enhanced MOSFET, is obtained by the self-aligned planar Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency.

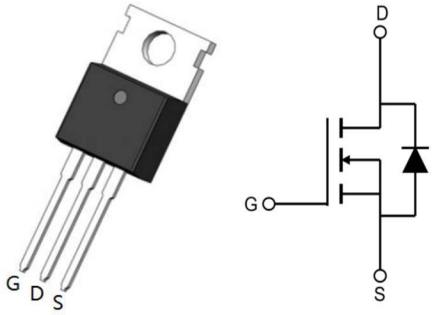
Product Summary

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
1000	4.3 at V_{GS} = 10 V	4.0

Features

- Low gate charge
- Fast Switching Speed
- High input resistance

TO-220 Pin Configuration



Applications

- Electronic Ballast
- Electronic Transformer
- LED Driver

Absolute Maximum Ratings Tc=25℃ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	1000	V
V_{GS}	Gate-Source Voltage	±30	V
I_D	Drain Current – Continuous (T_C=25℃)	4.0	A
	Drain Current – Continuous (T_C=100℃)	1.5	A
I_{DM}	Drain Current – Pulsed[1]	15	A
P_D	Power Dissipation (T_C=25℃)	33	W
	Power Dissipation (T_C=100℃)	1.5	W/℃
T_{STG}	Storage Temperature Range	-50 to 150	℃
T_J	Operating Junction Temperature Range	-50 to 150	℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	℃/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	2.6	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	1000	---	---	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=1000V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=1000V , V_{GS}=0V , T_J=125℃	---	---	10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±30V , V_{DS}=0V	---	---	±100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=1.5A	---	4.2	5.6	Ω
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	3.0	4.0	5.0	V
gfs	Forward Transconductance	V_{DS}=10V , I_S=3A	---	8.0	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge	V_{DS}=500V , V_{GS}=10V , I_D=2.0A	---	23.7	---	nC
Q_{gs}	Gate-Source Charge		---	2.9	---	
Q_{gd}	Gate-Drain Charge		---	11	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DS}=500V,R_L=3.3Ω V_{GS}=10V,R_G=25Ω	---	33	---	ns
T_r	Rise Time		---	42	---	
$T_{d(off)}$	Turn-Off Delay Time		---	26	---	
T_f	Fall Time		---	30	---	
C_{iss}	Input Capacitance	V_{DS}=25V , V_{GS}=0V , F=1MHz	---	600	---	pF
C_{oss}	Output Capacitance		---	49	---	
C_{rss}	Reverse Transfer Capacitance		---	5.0	---	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	2.5	A
I_{SM}	Pulsed Source Current		---	---	8.0	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V

Note :

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics (Curves)

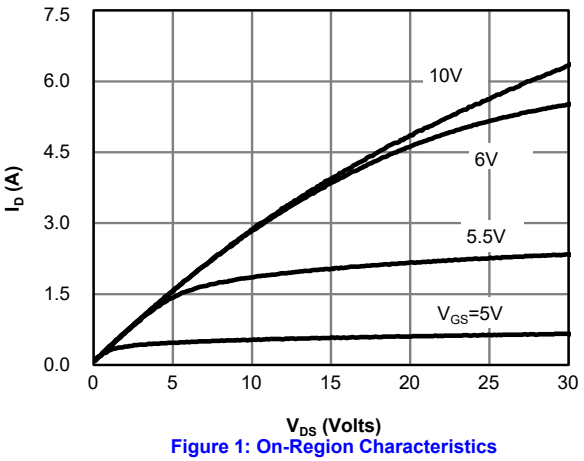


Figure 1: On-Region Characteristics

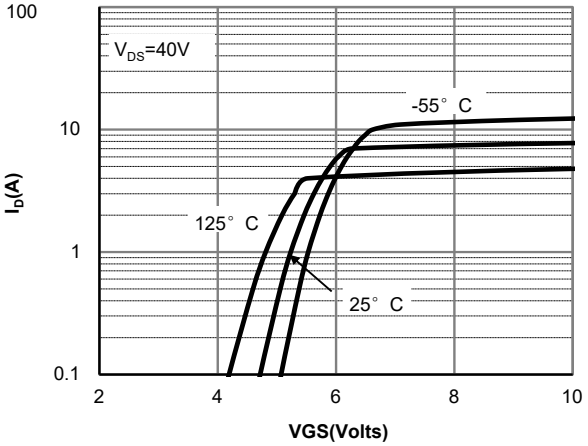


Figure 2: Transfer Characteristics

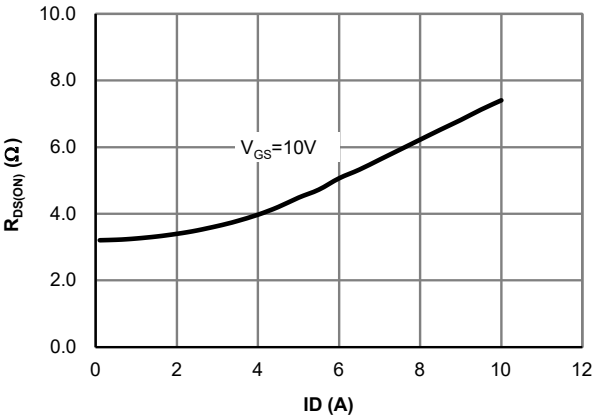


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

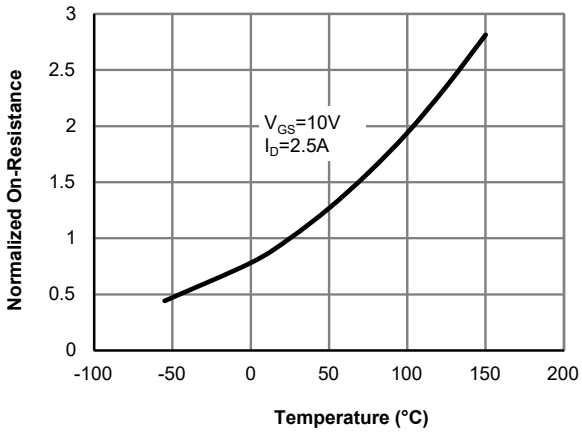


Figure 4: On-Resistance vs. Junction Temperature

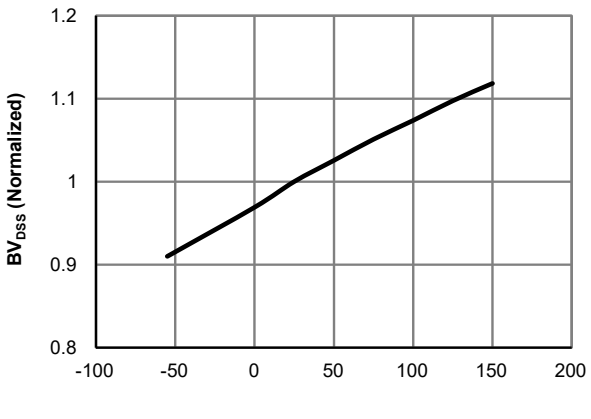


Figure 5:Break Down vs. Junction Temperature

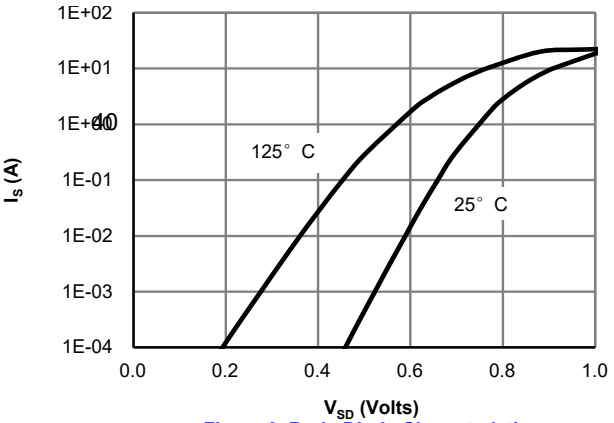


Figure 6: Body-Diode Characteristics

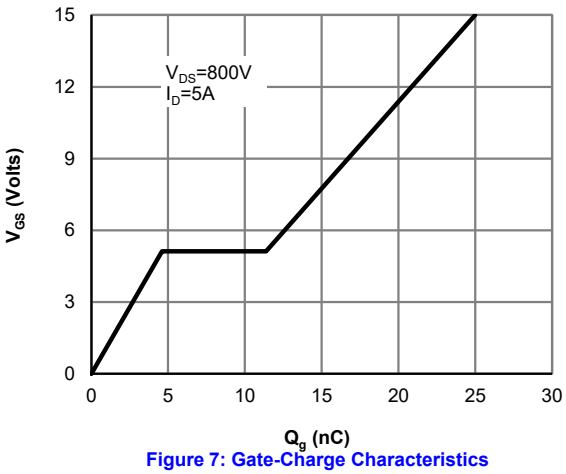


Figure 7: Gate-Charge Characteristics

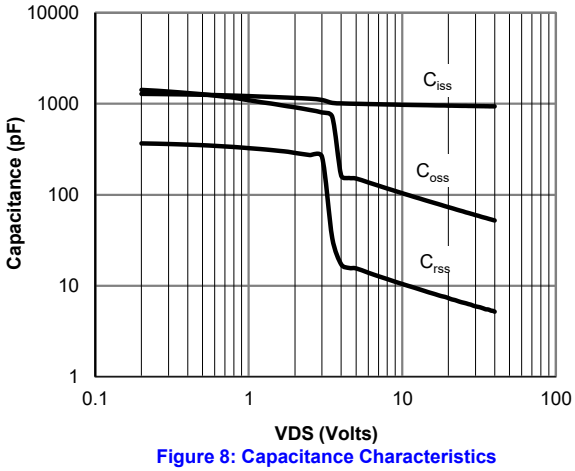


Figure 8: Capacitance Characteristics

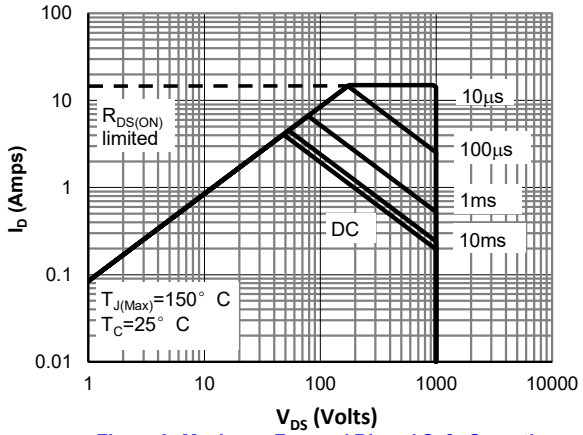


Figure 9: Maximum Forward Biased Safe Operating

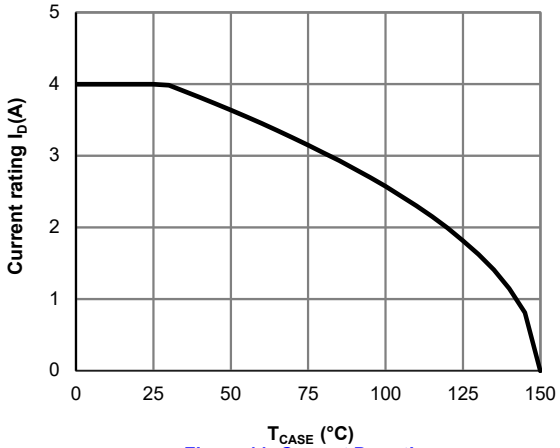


Figure 11: Current De-rating

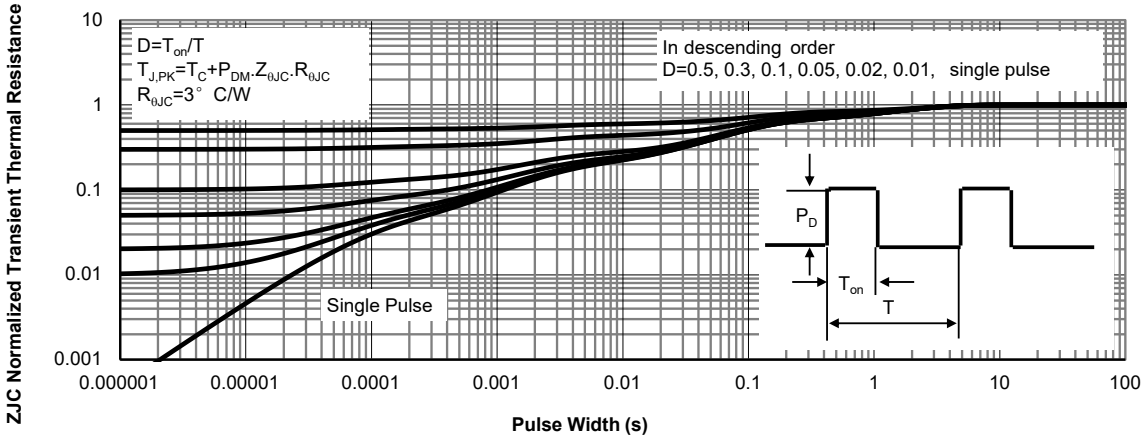


Figure 13: Normalized Maximum Transient Thermal Impedance

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